

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-26 (Cancelled).

Claim 27 (Currently Amended): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

- a) depositing a second thin layer ~~on the~~ covering said first thin layer;
- b) engraving or lithography of the second thin layer, as a function of a desired ~~correction or corrections~~;
- c) etching the second sub-layer through the first sub-layer.

Claim 28 (Currently Amended): A correction method as claimed in claim 27, the desired ~~correction~~ corrections including an addition of ~~one or more~~ several patterns.

Claim 29 (Currently Amended): A correction method as claimed in Claim 27, in which ~~one or more~~ several patterns are missing from the design, the engraving or lithography including reproduction in the second thin layer of the missing patterns.

Claim 30 (Previously Presented): A correction method as claimed in Claim 27, further comprising d) etching the first sub-layer through the second thin layer after the engraving or lithography b) and prior to the etching c).

Claim 31 (Previously Presented): A correction method as claimed in claim 30, further comprising removing the second thin layer after the etching d) of the first sub-layer through the second thin layer and prior to the etching c).

Claim 32 (Currently Amended): A correction method as claimed in Claim 27, the correction including removing ~~one or more~~ several patterns.

Claim 33 (Currently Amended): A correction method as claimed in Claim 32, in which the ~~one or more~~ several patterns are in excess, the engraving or lithography in the second thin layer leaving one or more blocks filling the patterns in excess.

Claim 34 (Previously Presented): A correction method as claimed in Claim 27, the correction including adding one or more missing patterns, then eliminating one or more other patterns in excess.

Claim 35 (Previously Presented): A correction method as claimed in Claim 34, further comprising, after the engraving or lithography b) and prior to the etching c):  
etching the first sub-layer through the second thin layer;  
removing the second thin layer;  
depositing a third thin layer on the first sub-layer; and  
second lithography in the third thin layer leaving blocks filling the patterns in excess.

Claim 36 (Previously Presented): A correction method as claimed in Claim 35, the third thin layer being a dielectric layer.

Claim 37 (Previously Presented): A correction method as claimed in Claim 36, the third thin layer being a resin or polymer layer.

Claim 38 (Previously Presented): A correction method as claimed in Claim 35, the third thin layer being a positive or negative photosensitive resin layer.

Claim 39 (Previously Presented): A correction method as claimed in Claim 35, further comprising removing the third thin layer after the etching c).

Claim 40 (Previously Presented): A correction method as claimed in Claim 27, further comprising removing the first sub-layer after the etching c) of the second sub-layer through the first sub-layer.

Claim 41 (Previously Presented): A correction method as claimed in Claim 27, in which the first sub-layer is based on a first conductive, or semiconductive, or insulating material, and the second sub-layer located between the substrate and the first sub-layer is based on a second conductive, or semiconductive, or insulating material different from the first material.

Claim 42 (Previously Presented): A correction method as claimed in Claim 27, in which the first sub-layer is a sacrificial layer.

Claims 43-45 (Cancelled).

Claim 46 (Previously Presented): A method as claimed in Claim 27, the second thin layer being a dielectric layer.

Claim 47 (Previously Presented): A method as claimed in Claim 27, the second thin layer being a resin or polymer layer.

Claim 48 (Previously Presented): A method as claimed in Claim 27, the engraving or lithography being carried out by direct writing.

Claim 49 (Previously Presented): A method as claimed in Claim 27, the engraving or lithography being carried out by one or more optical particle beams.

Claim 50 (Previously Presented): A method as claimed in Claim 49, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 51 (Previously Presented): A method as claimed in Claim 49, the beam being controlled by a digital device associated with a data medium including data relative to the erroneous design and to a desired corrected design.

Claim 52 (Previously Presented): A lithography device carrying out one or more of the lithography of the method as claimed in Claim 27, comprising:

first means for producing at least one lithography beam;

second means for processing data relative to an erroneous design formed in a thin layer, and data relative to a desired corrected design, and for producing correction data following such processing; and

third means for controlling the first means, from correction data produced by the second means.

Claim 53 (Previously Presented): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the

erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

- a) depositing a second thin layer on the first thin layer;
- b) engraving or lithography of the second thin layer, as a function of a desired correction or corrections, etching the first sub-layer through the second thin layer;  
removing the second thin layer after the etching of the first sub-layer through the second thin layer; and
- c) etching the second sub-layer through the first sub-layer.

Claim 54 (Previously Presented): A method as claimed in Claim 53, the second thin layer being a resin or polymer layer.

Claim 55 (Previously Presented): A method as claimed in Claim 53, the engraving or lithography being carried out by one or more optical particle beams.

Claim 56 (Previously Presented): A method as claimed in Claim 55, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 57 (Previously Presented): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

- a) depositing a second thin layer on the first thin layer;
- b) engraving or lithography of the second thin layer, as a function of a desired correction or corrections,

etching the first sub-layer through the second thin layer;  
removing the second thin layer;  
depositing a third thin layer on the first sub-layer; and  
second lithography in the third thin layer leaving blocks filling the patterns in excess;  
and  
c) etching the second sub-layer through the first sub-layer.

Claim 58 (Previously Presented): A method as claimed in Claim 57, the engraving or lithography being carried out by one or more optical particle beams.

Claim 59 (Previously Presented): A method as claimed in Claim 58, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 60 (Currently Amended): A method ~~as claimed in Claim 27~~ for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

a) depositing a second thin layer on the first thin layer;  
b) engraving or lithography of the second thin layer, as a function of a desired  
corrections; and

c) etching the second sub-layer through the first sub-layer,  
wherein said step of depositing said second thin layer on said first thin layer is performed such that said second thin layer covers at least a portion of said first sub-layer thereby covering said erroneous design.

Claim 61 (Currently Amended): A method ~~as claimed in Claim 27~~ for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

- a) depositing a second thin layer on the first thin layer;
- b) engraving or lithography of the second thin layer, as a function of a desired  
corrections; and
- c) etching the second sub-layer through the first sub-layer,

wherein said erroneous design comprises a plurality of erroneous patterns, each erroneous pattern being an erroneous presence or an erroneous absence of a hole in said first sub-layer, and wherein said step of depositing said second thin layer is performed such that said second thin layer covers said plurality of erroneous patterns in said first sub-layer.